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1/31

FIG. 1A

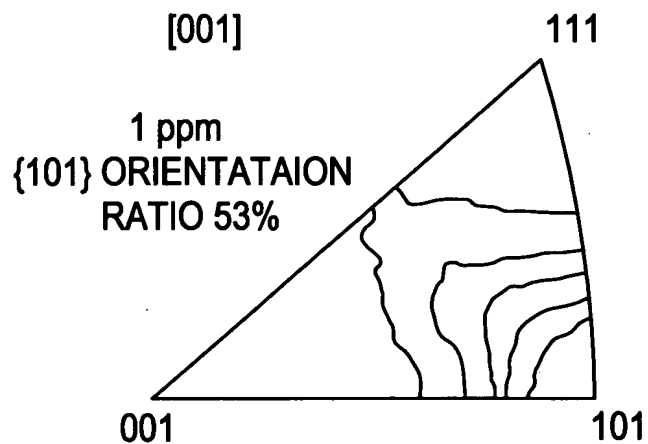


FIG. 1B

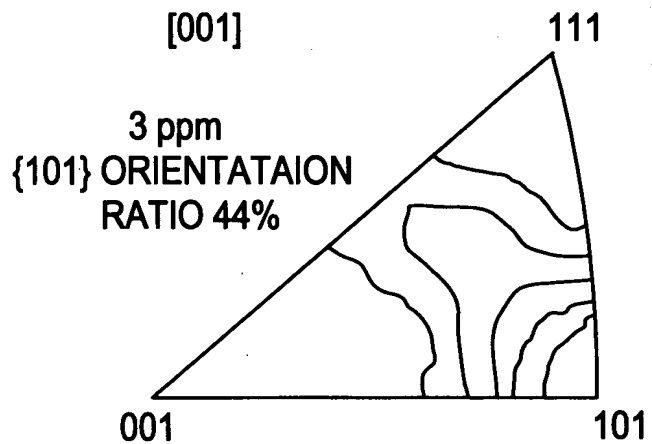


FIG. 1C

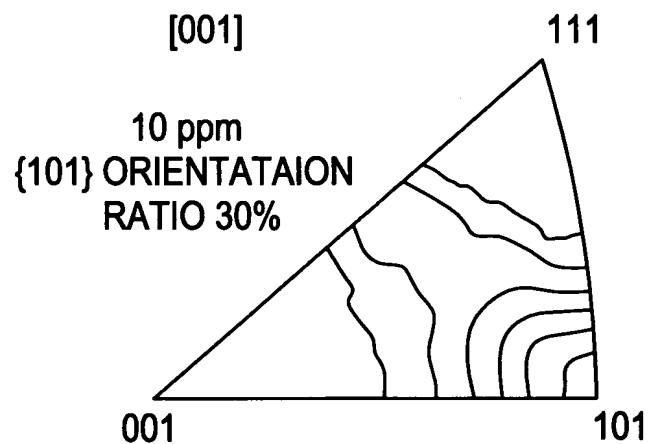


FIG. 1D

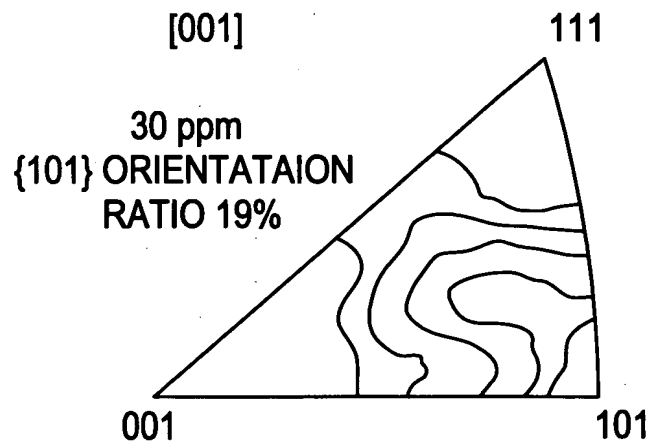
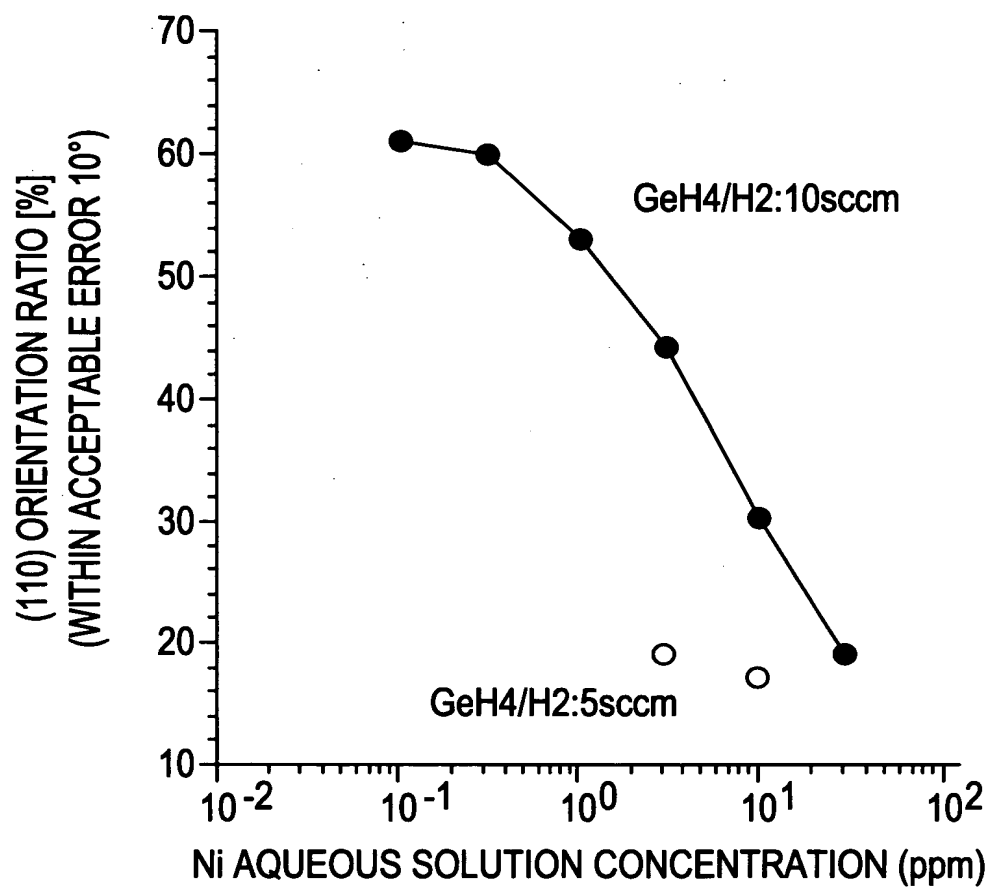




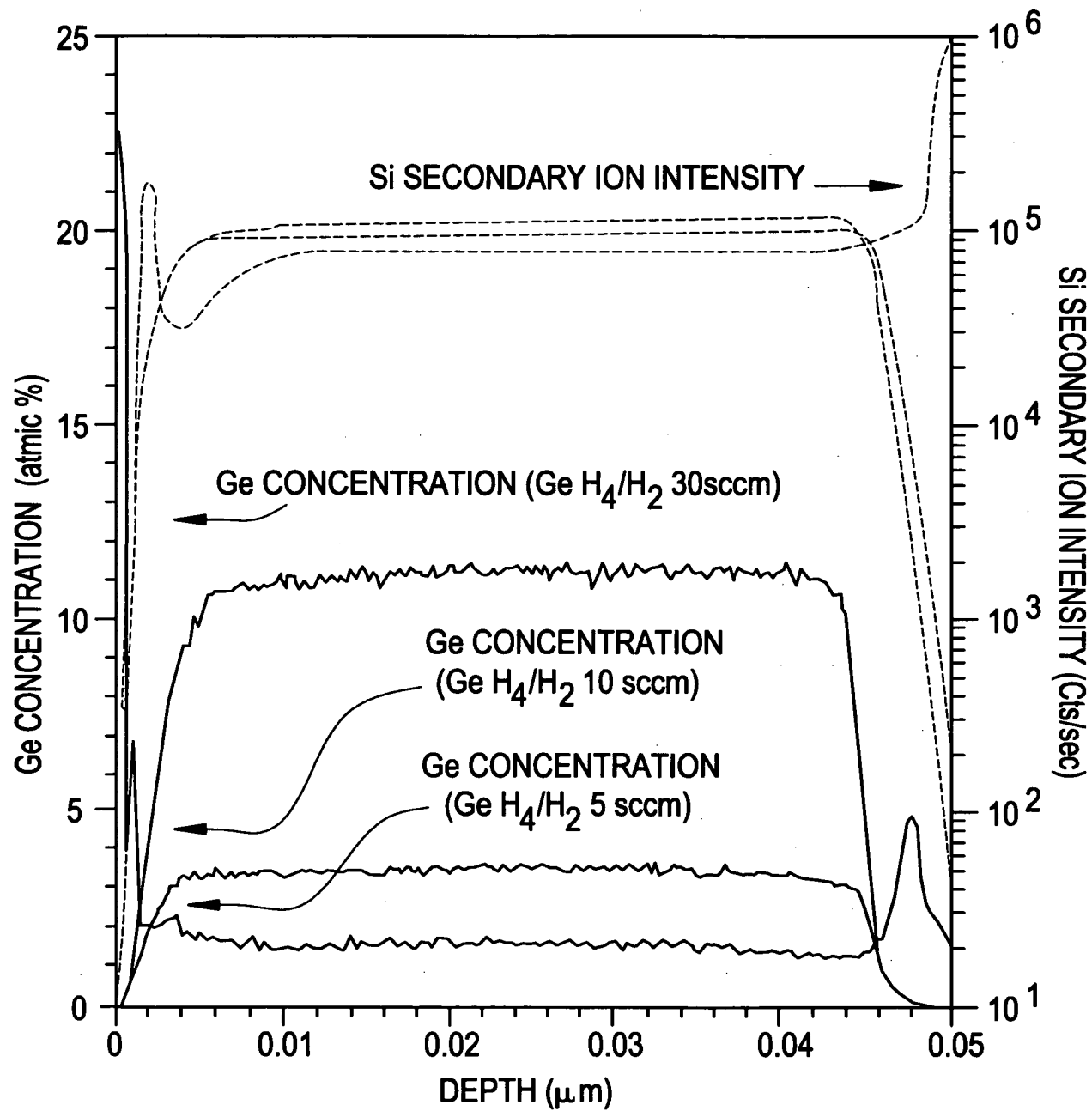
FIG. 2





3/31

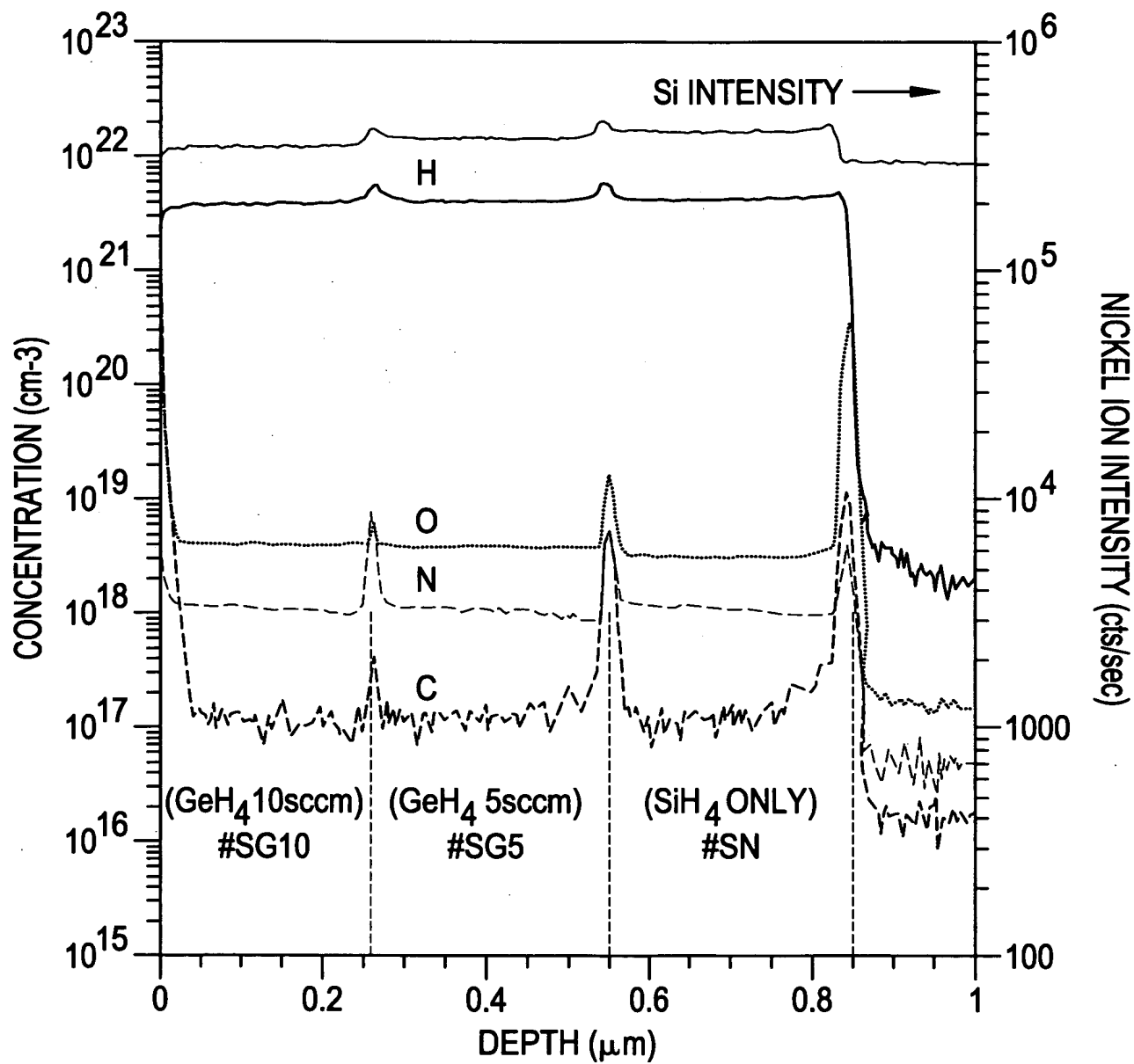
FIG. 3

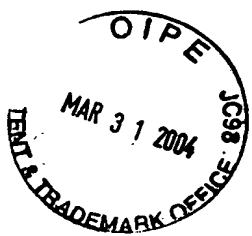




4/31

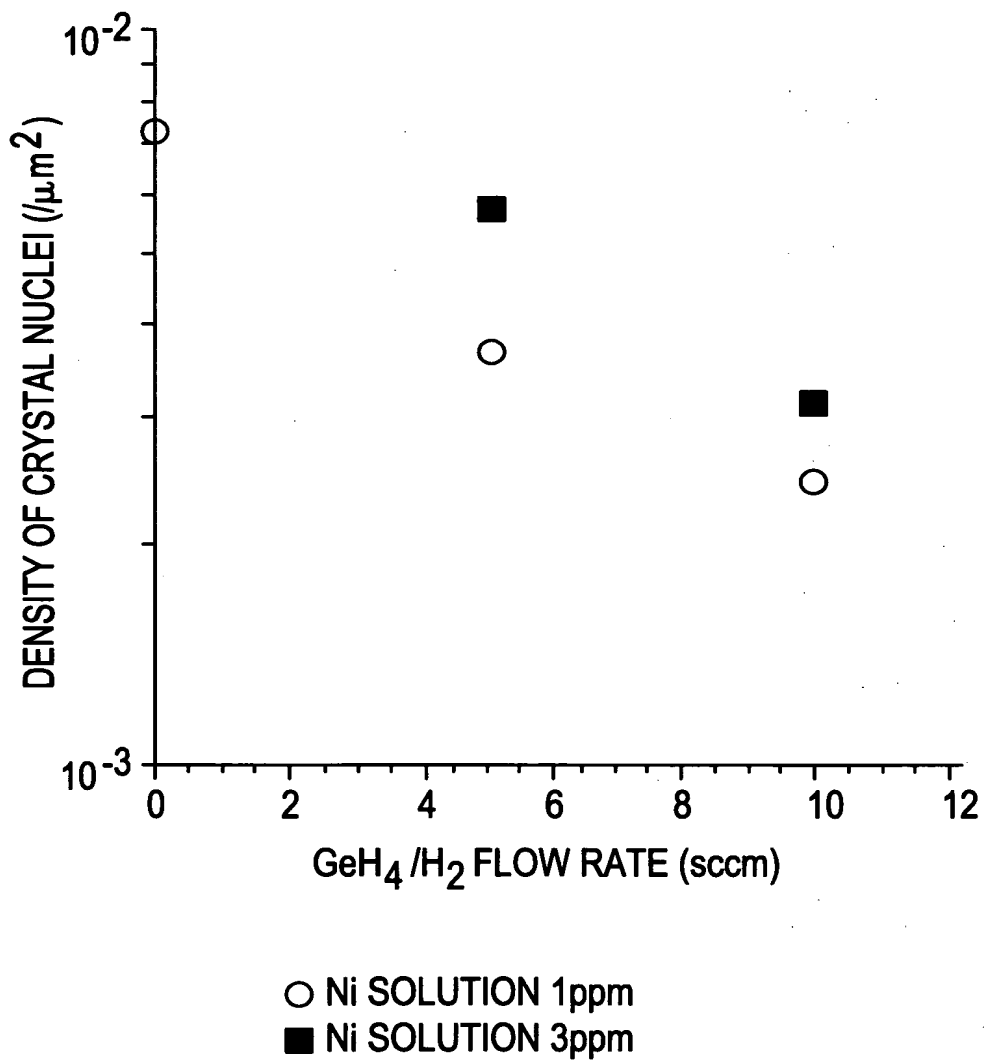
FIG. 4





5/31

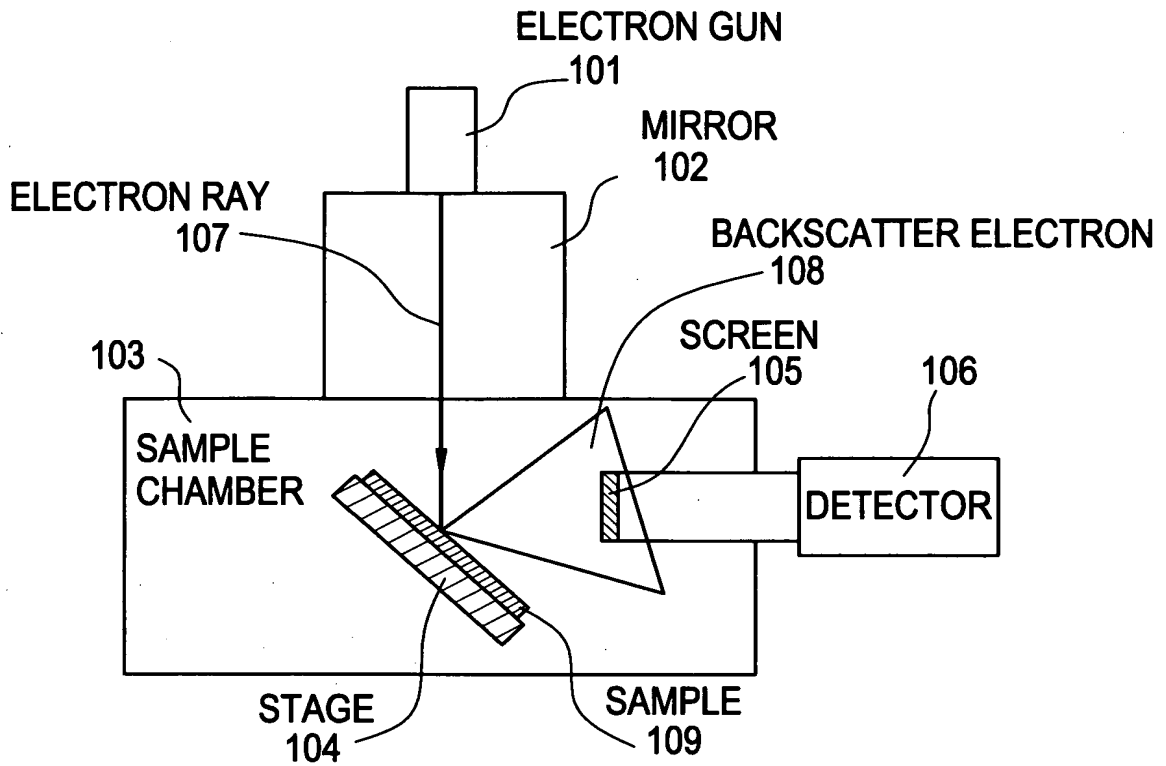
FIG. 5



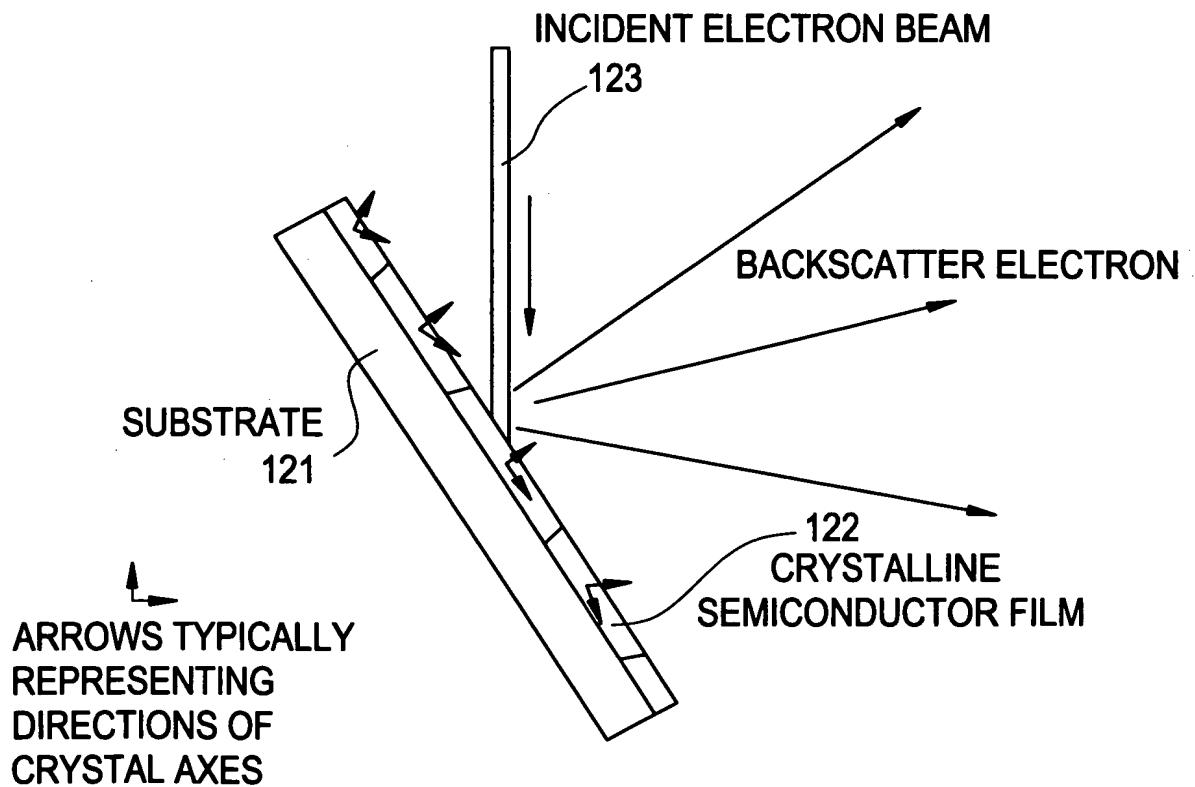


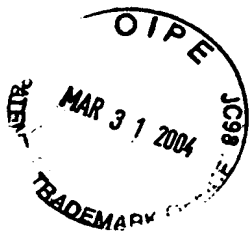
6/31

**FIG. 6**



**FIG. 7**

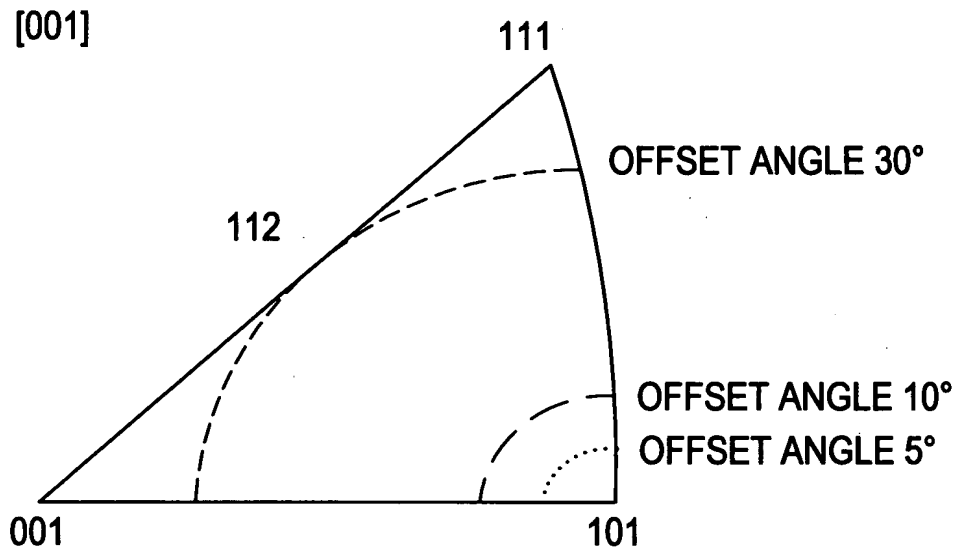




7/31

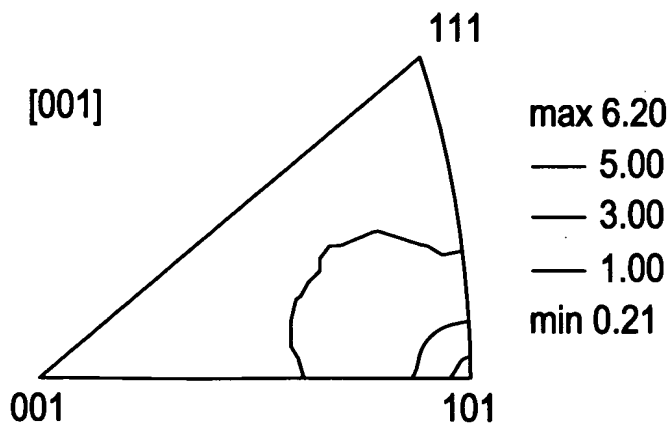
## FIG. 8A

PLOTS OF ALL OF MEASUREMENT POINTS  
IN MAPPING MEASUREMENT



## FIG. 8B

EXAMPLE OF TRANSLATING CONCENTRATION OF POINTS  
OF FIG. 8A INTO CONTOUR





8/31

FIG. 9

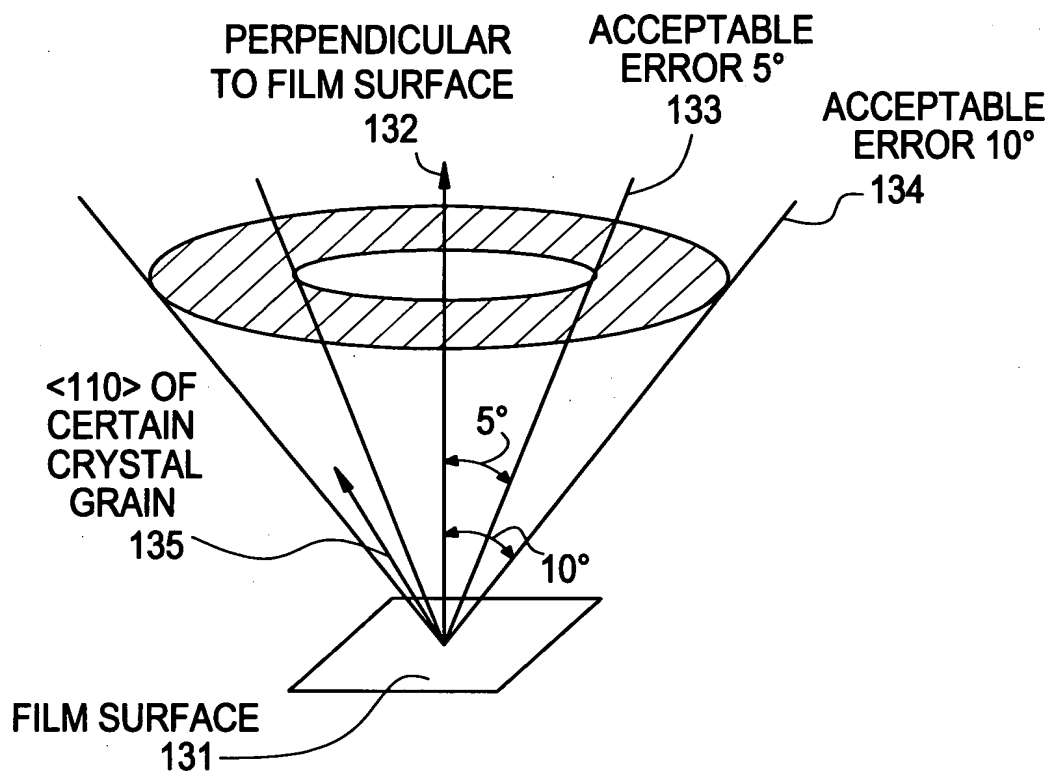
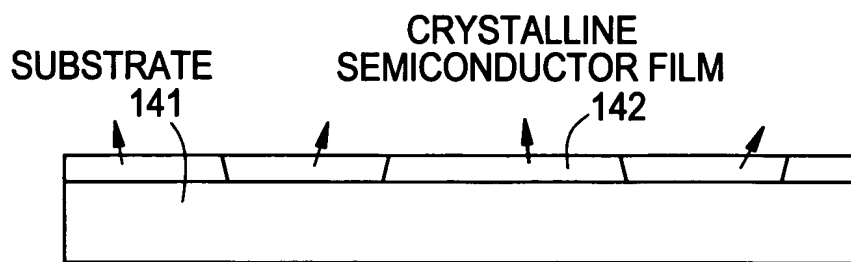


FIG. 10



VIEW EXPLAINING FLUCTUATION OF <101> ORIENTATION OF CRYSTAL GRAIN



9/31

FIG. 11A

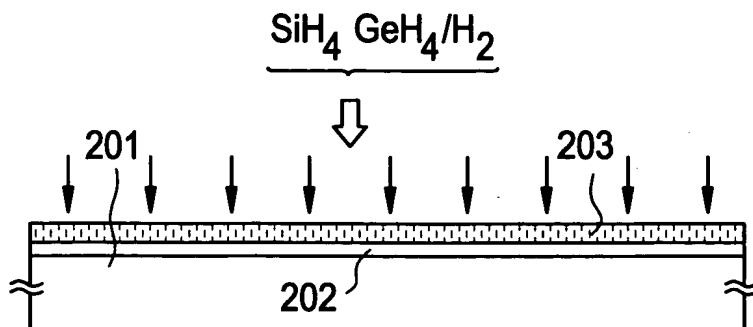


FIG. 11B

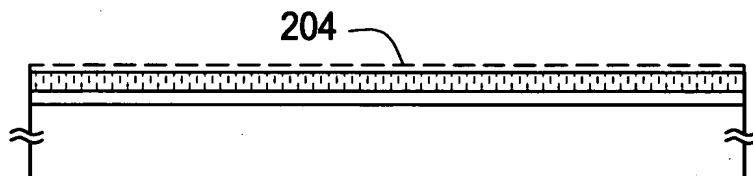


FIG. 11C

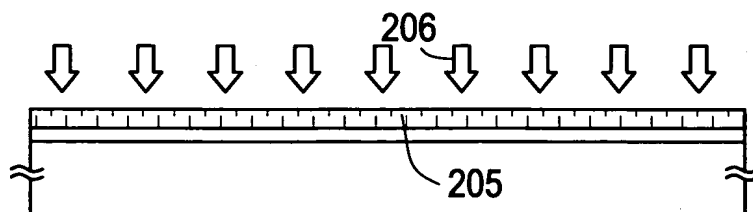
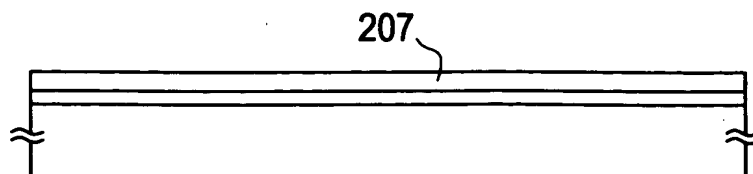


FIG. 11D



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10/31

FIG. 12A

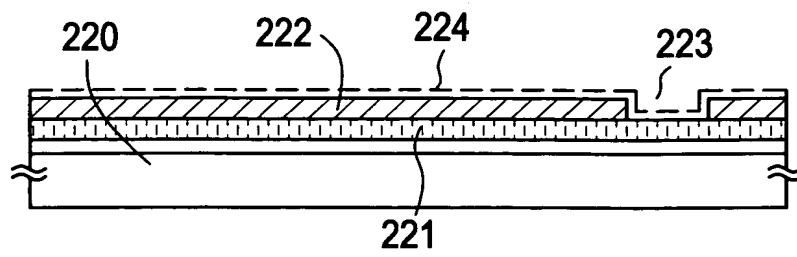


FIG. 12B

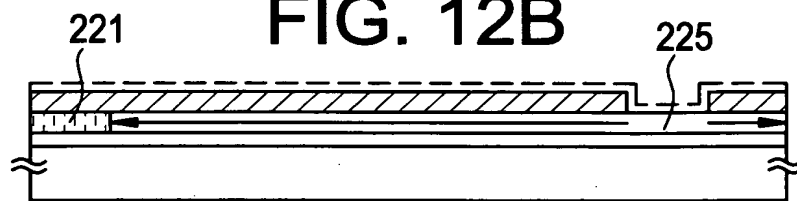


FIG. 12C

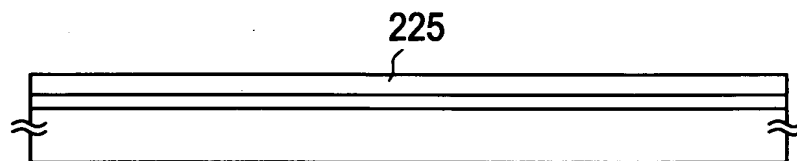


FIG. 13A

P ION IMPLANTATION

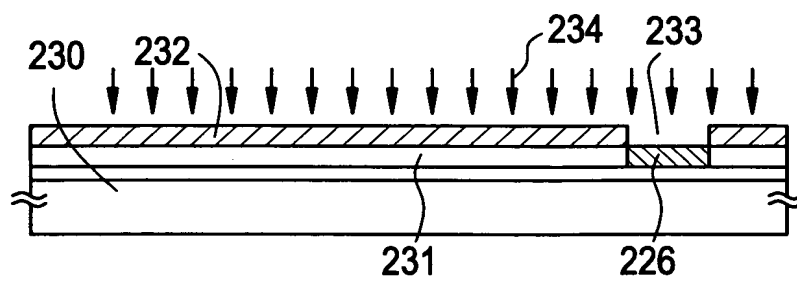


FIG. 13B

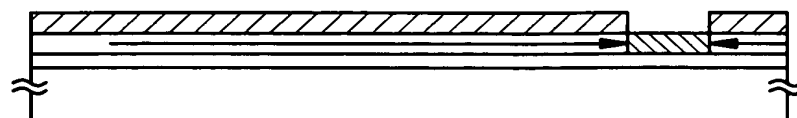
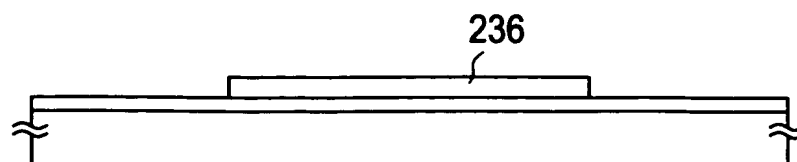


FIG. 13C



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11/31

FIG. 14A

B DOPING

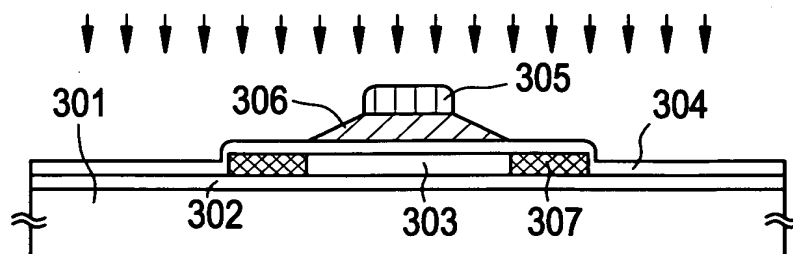


FIG. 14B

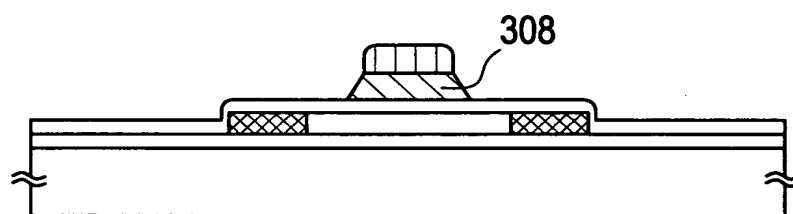


FIG. 14C

B DOPING

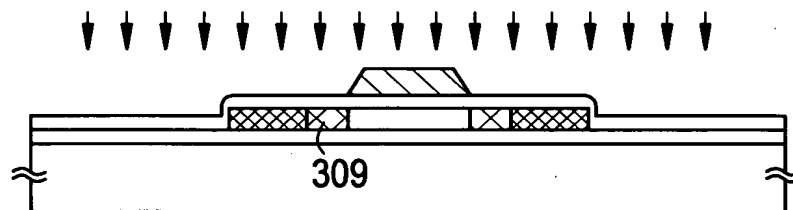
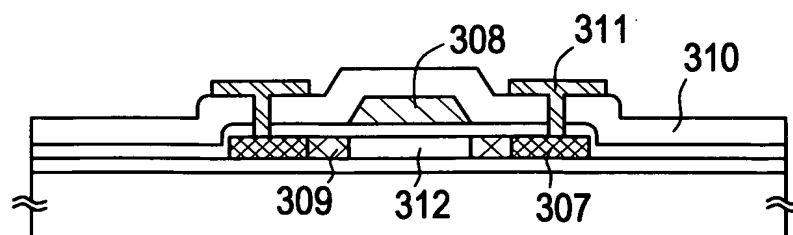


FIG. 14D



12/31

FIG. 15A

P DOPING

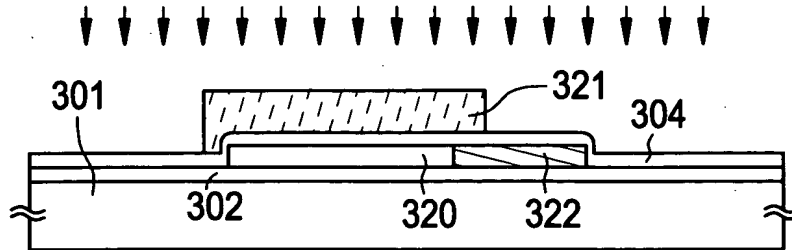


FIG. 15B

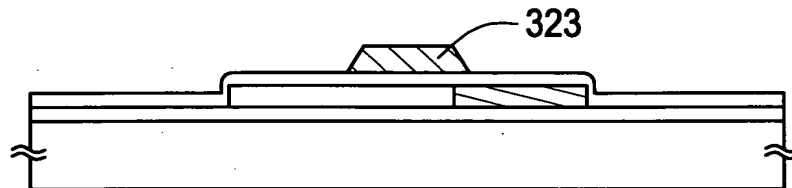


FIG. 15C

P DOPING

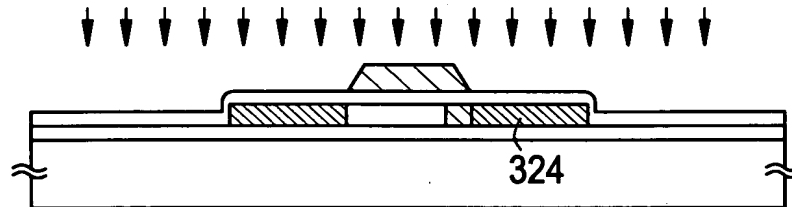


FIG. 15D

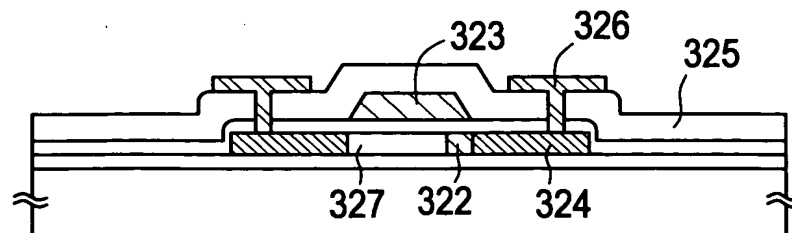


FIG. 16A

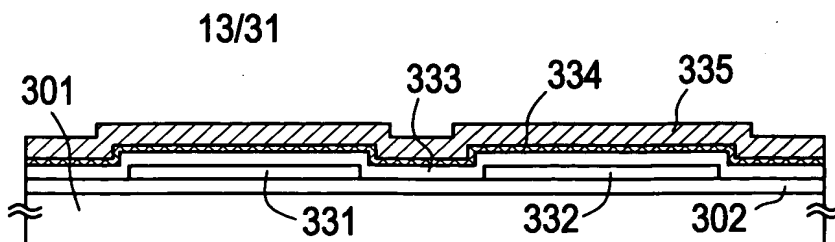


FIG. 16B

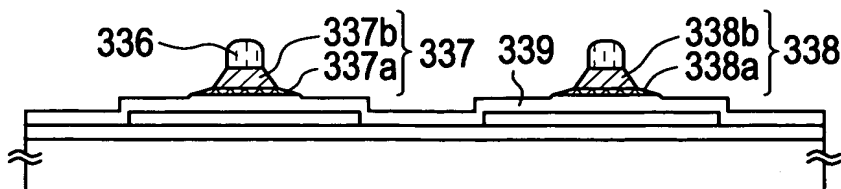


FIG. 16C

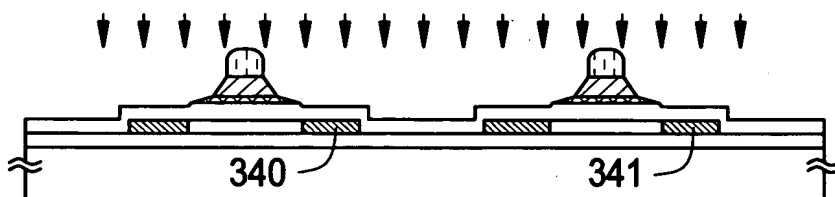


FIG. 16D

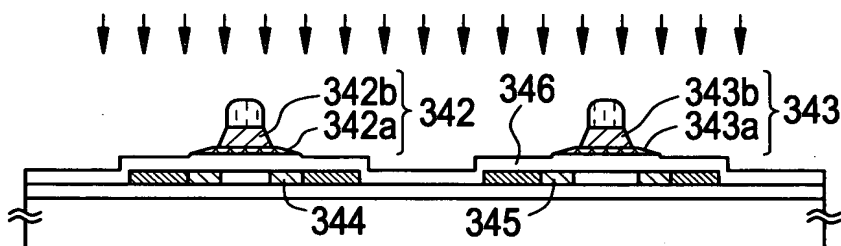


FIG. 16E

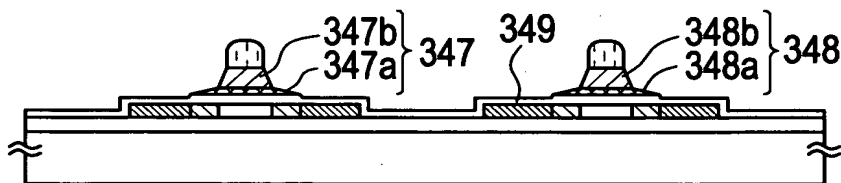


FIG. 16F

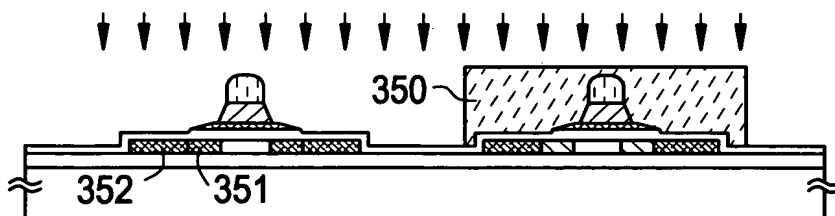


FIG. 16G

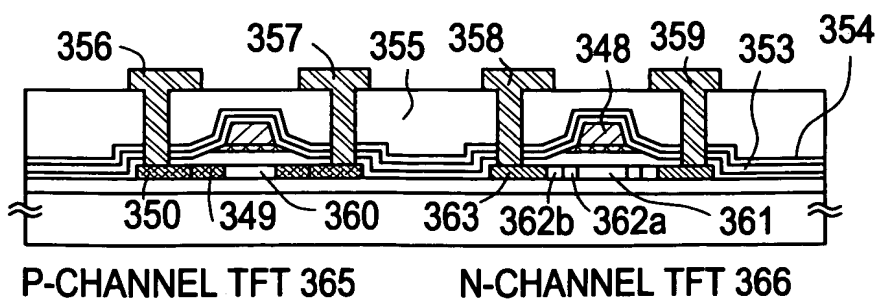
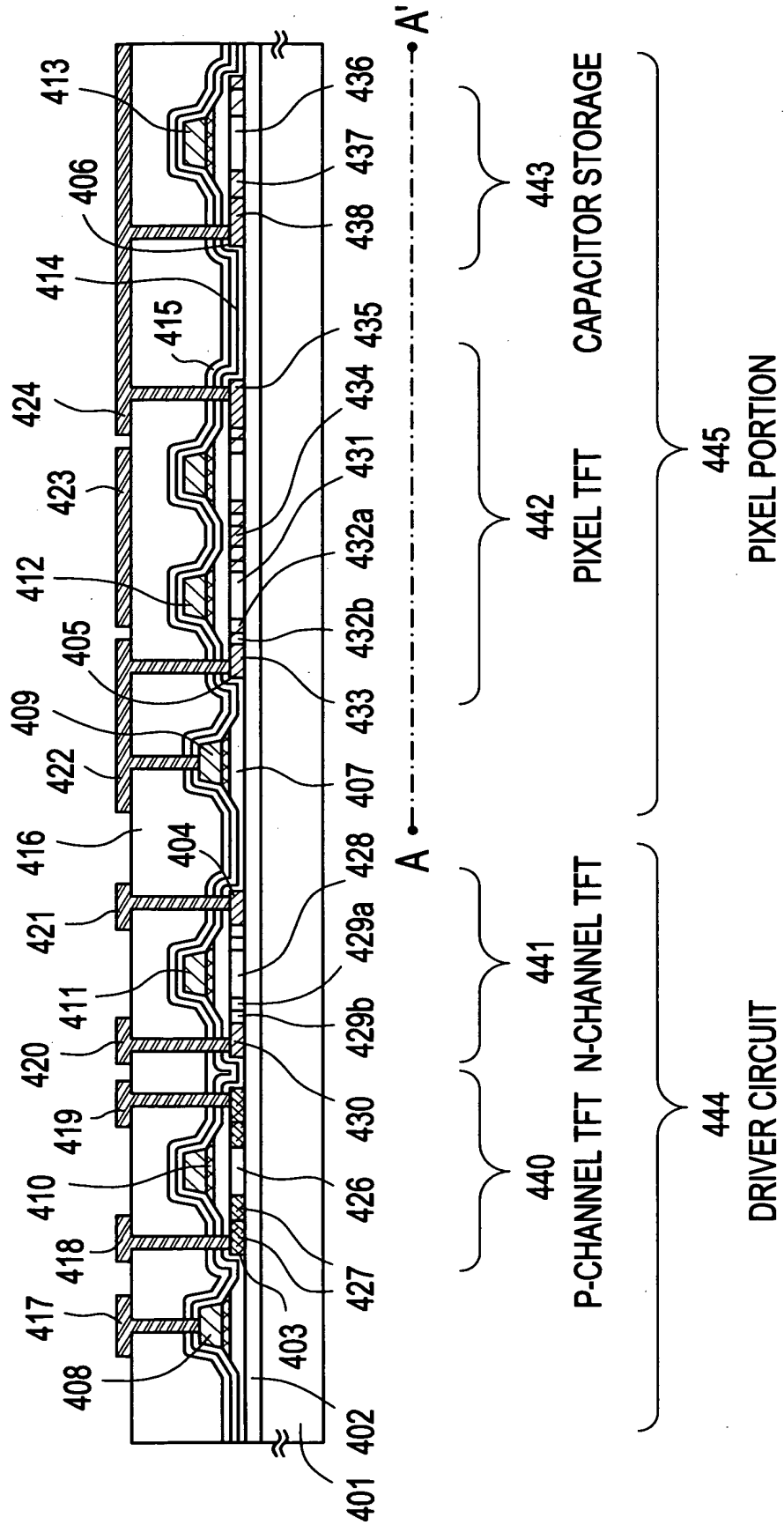


FIG. 17

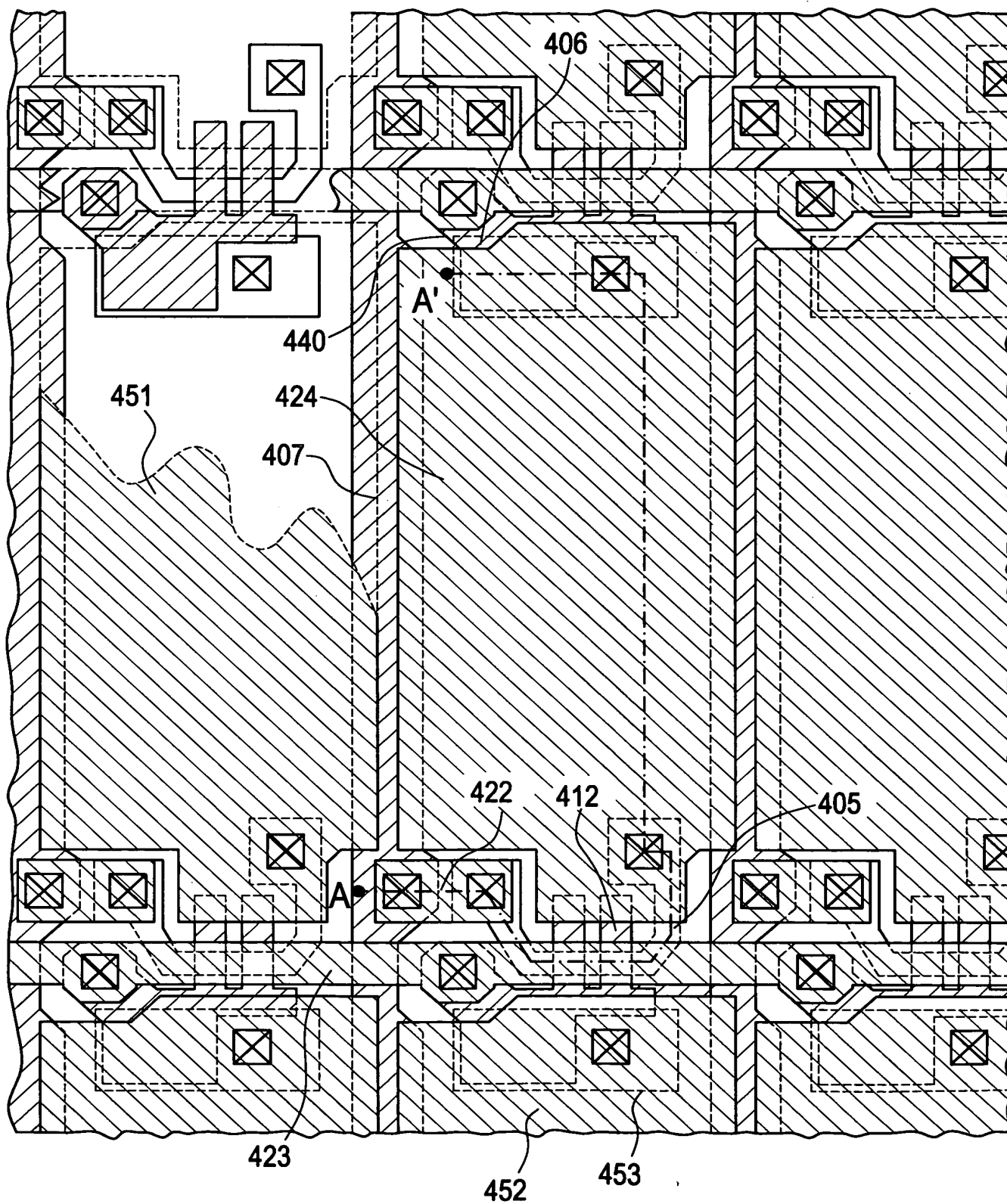


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15/31

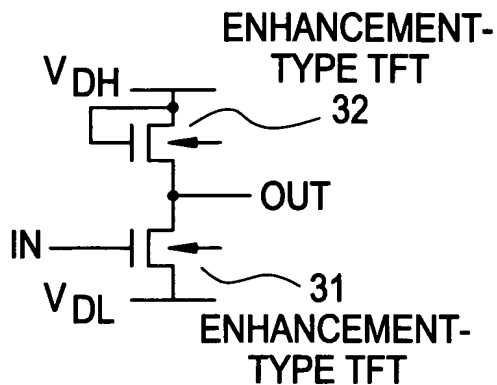
FIG. 18





**FIG. 19A**

EEMOS CIRCUIT

**FIG. 19B**

EDMOS CIRCUIT

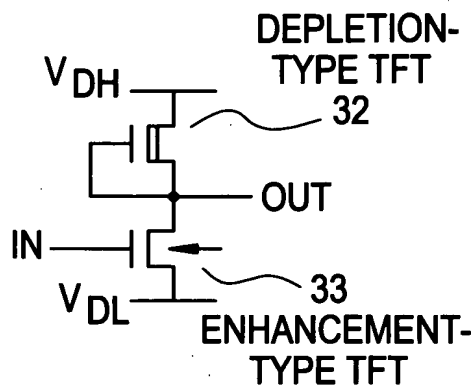
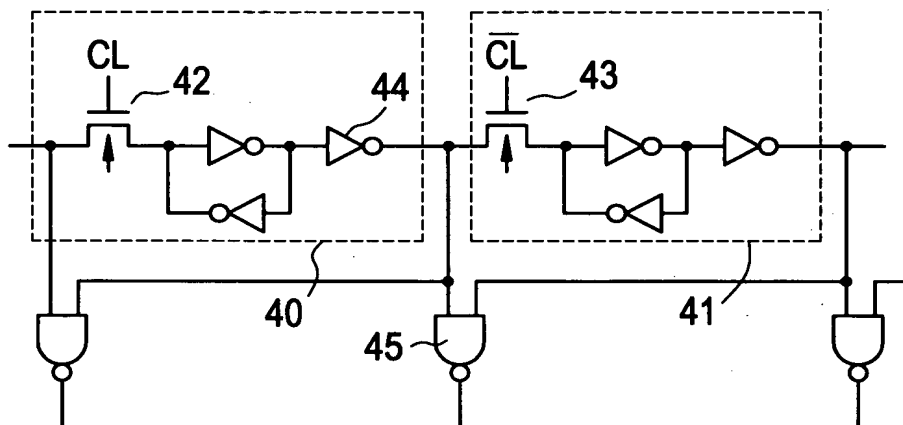
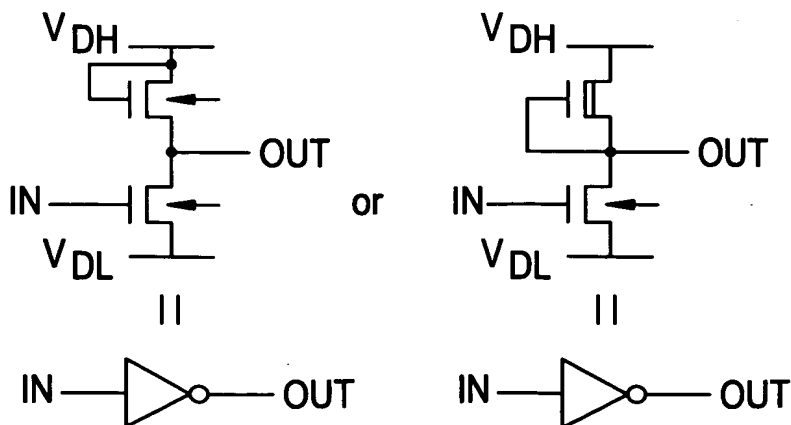
**FIG. 20A****FIG. 20B**

FIG. 21

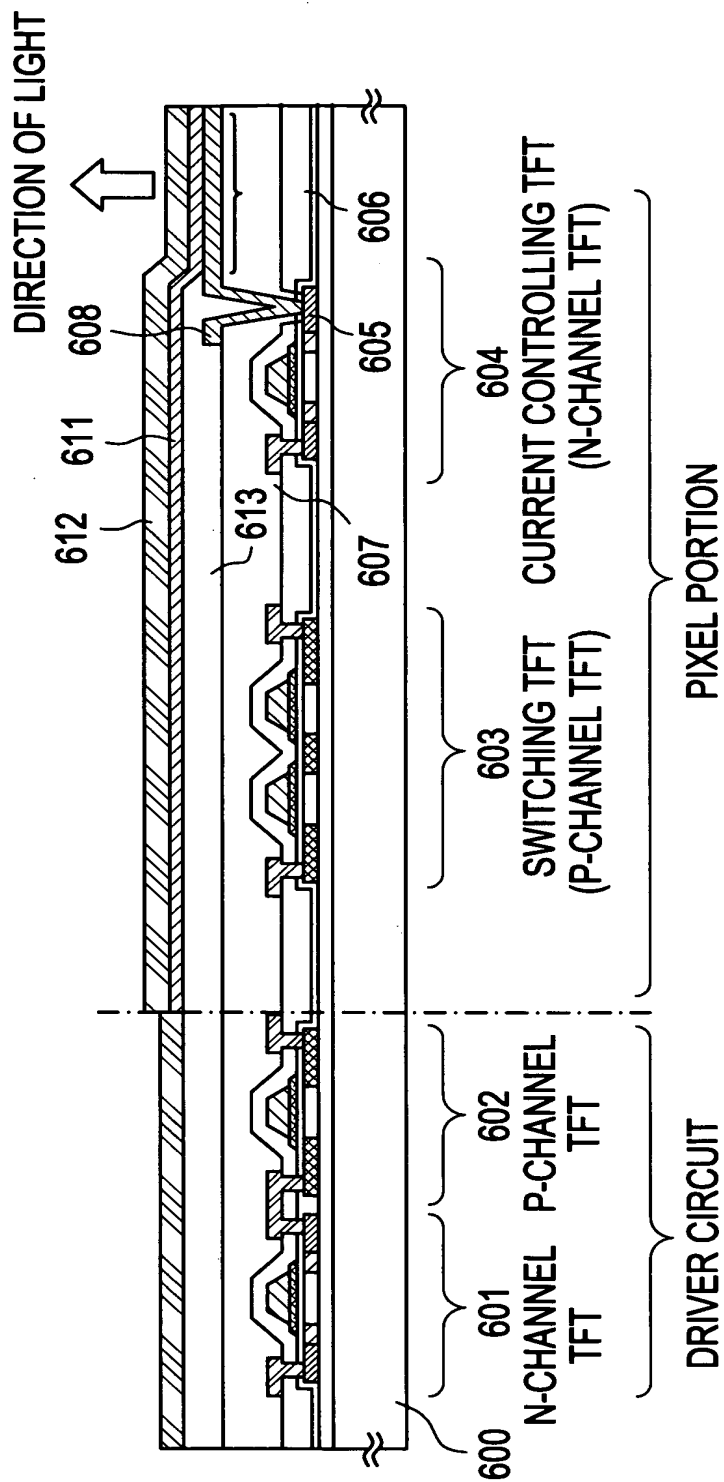




FIG. 22A

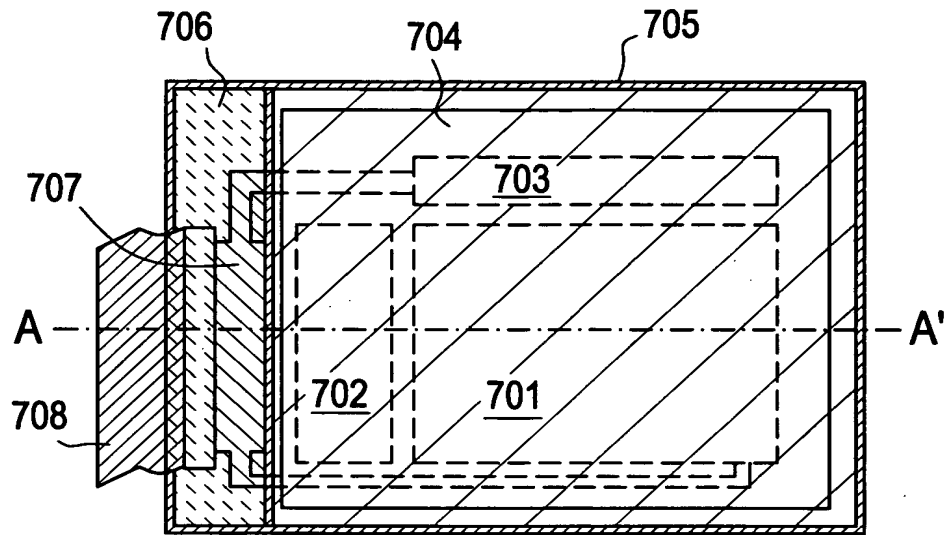
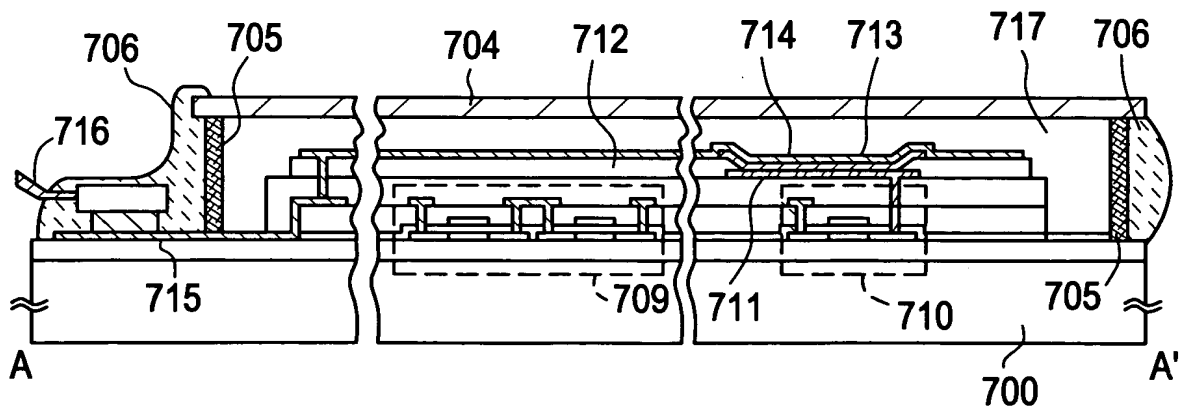


FIG. 22B





19/31

FIG. 23A

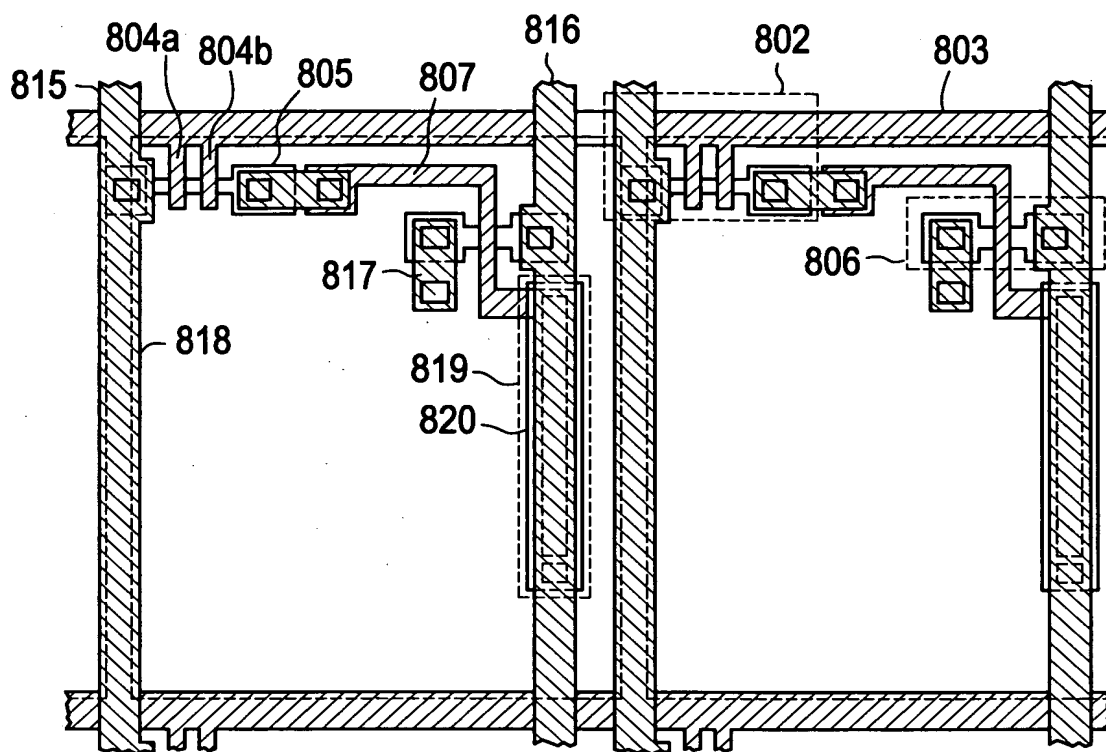


FIG. 23B

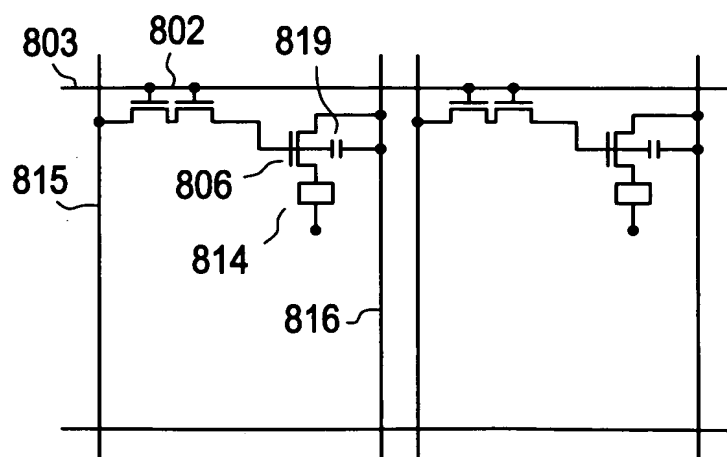




FIG. 24

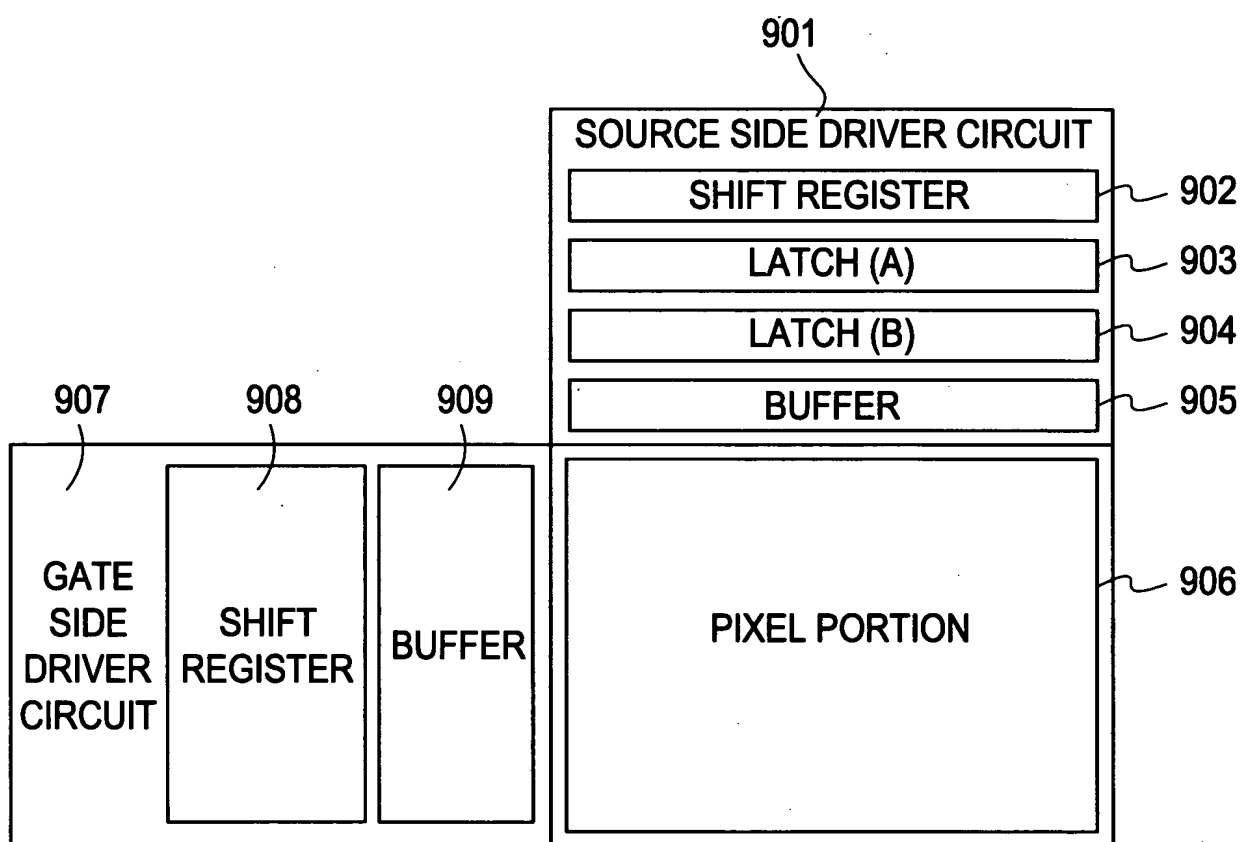


FIG. 25

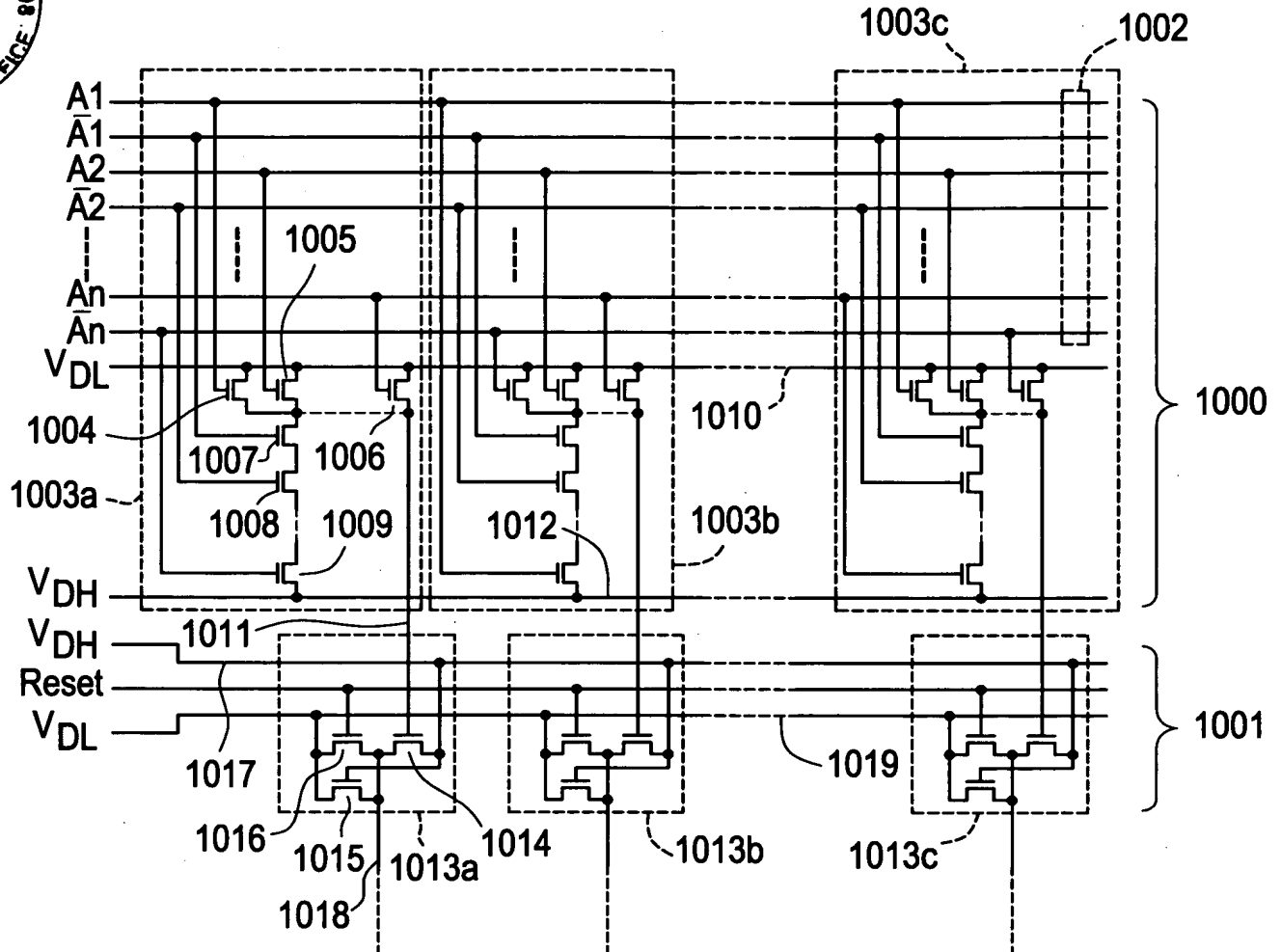


FIG. 26

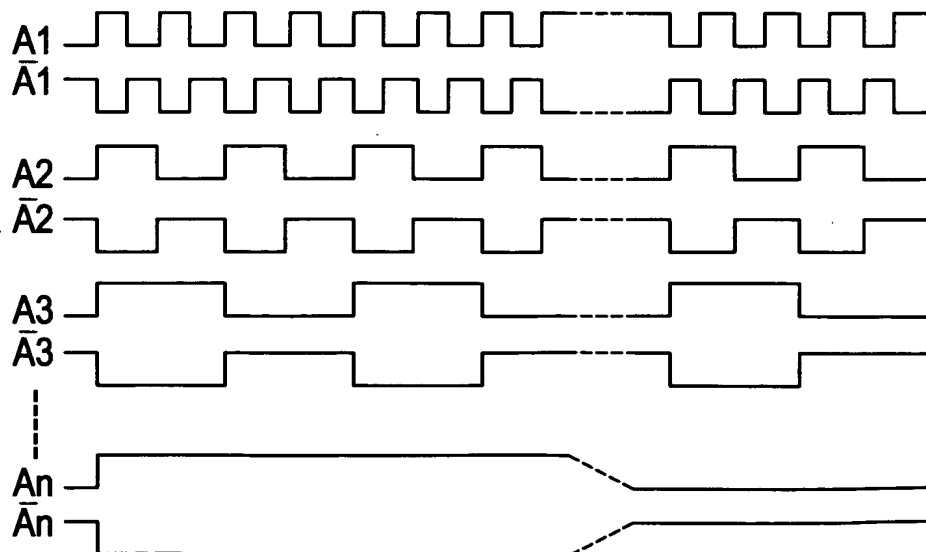


FIG. 27

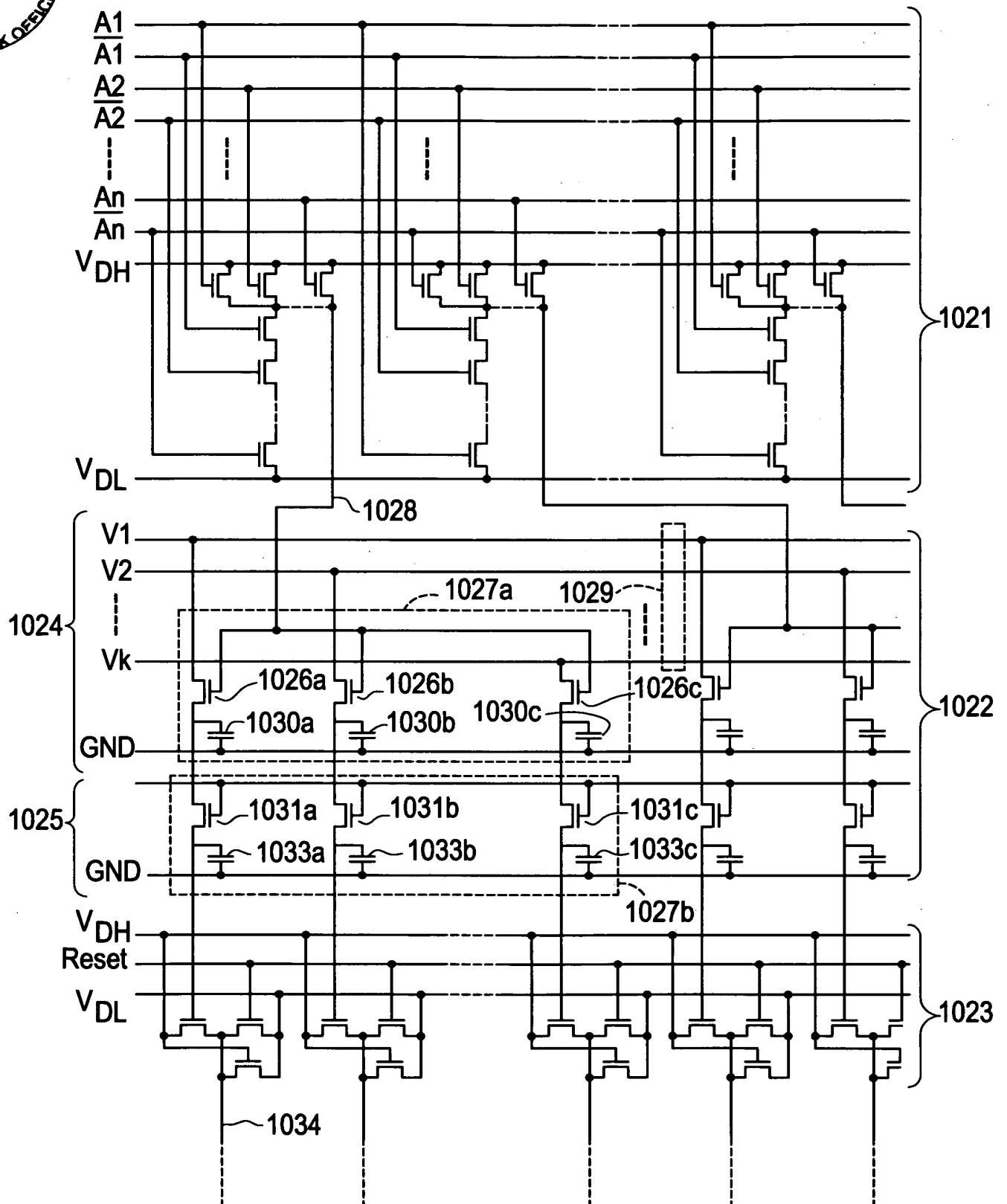


FIG. 28

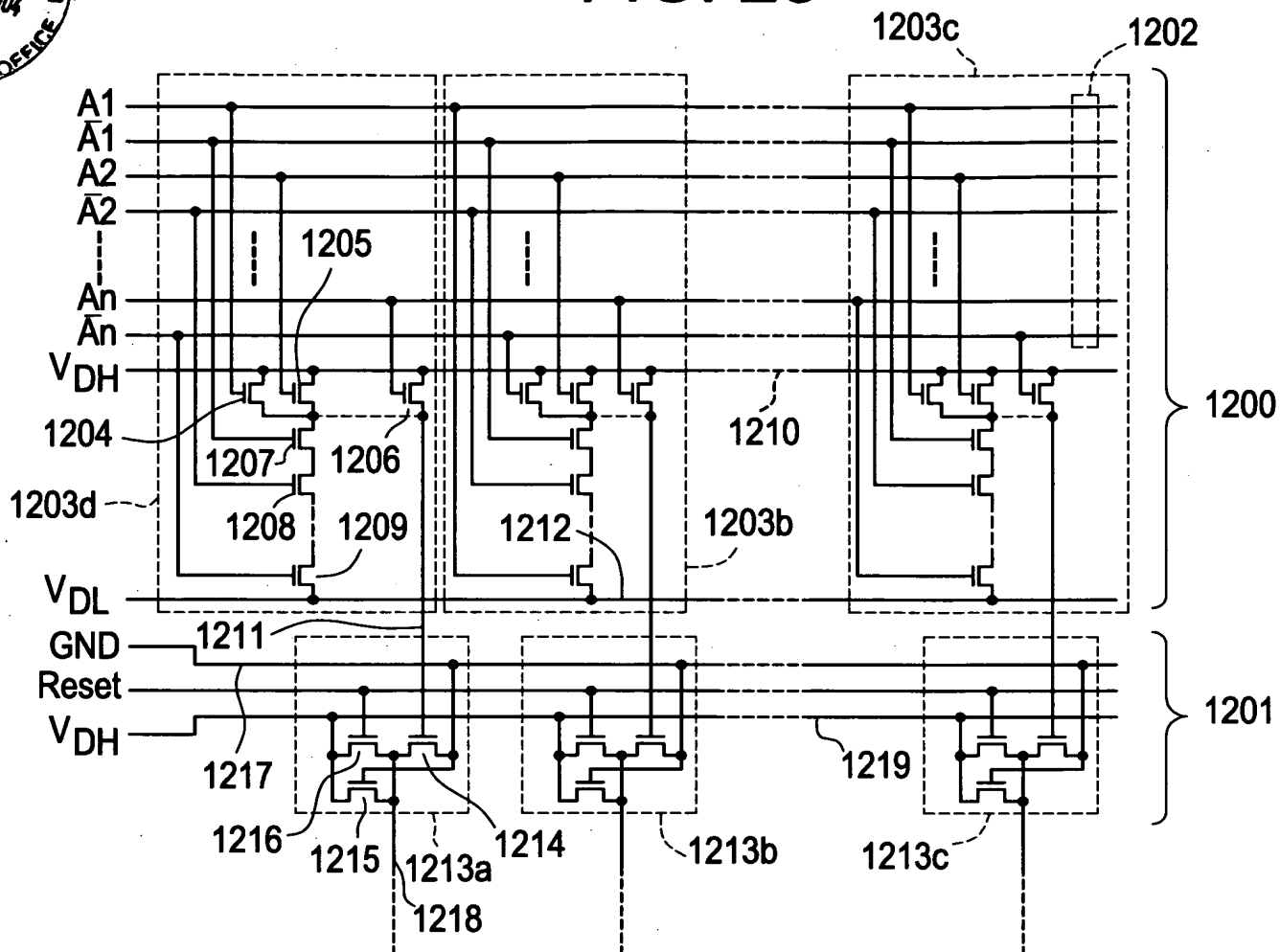
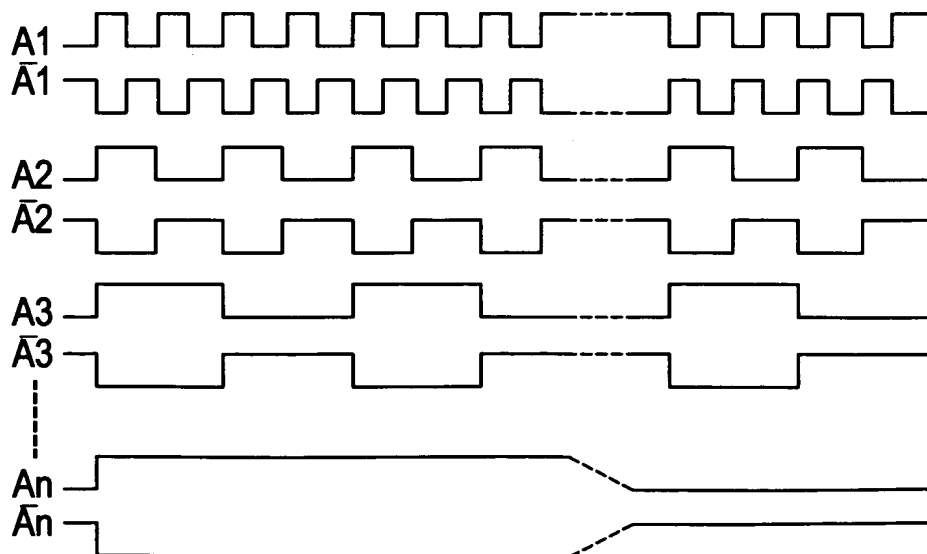


FIG. 29

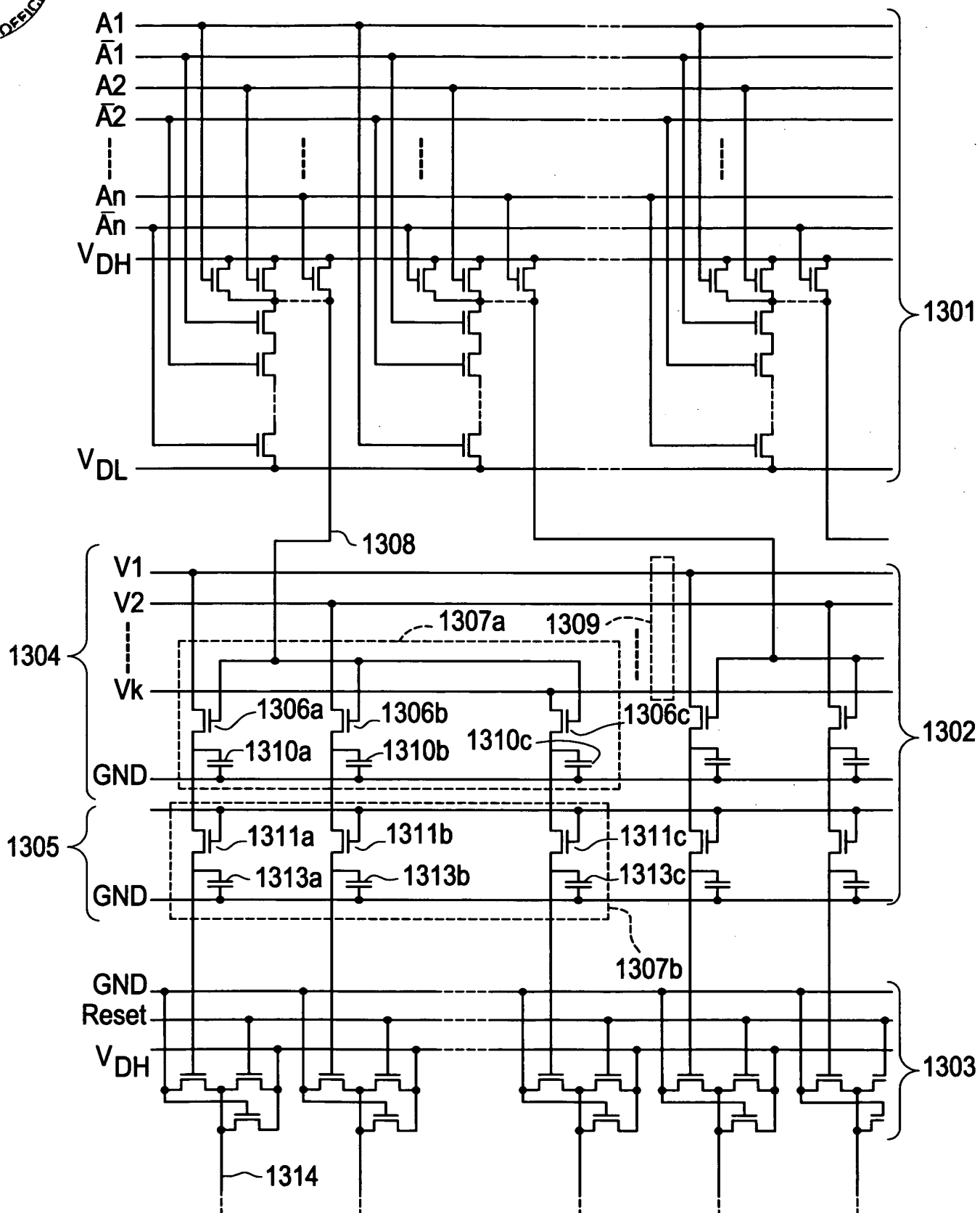






24/31

FIG. 30





25/31

FIG. 31A

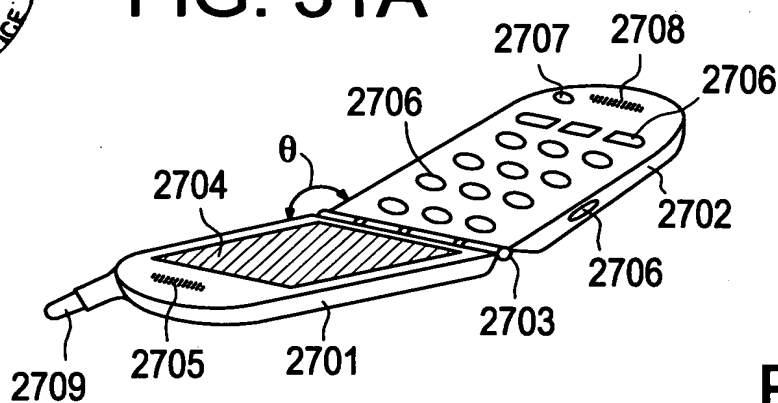


FIG. 31B

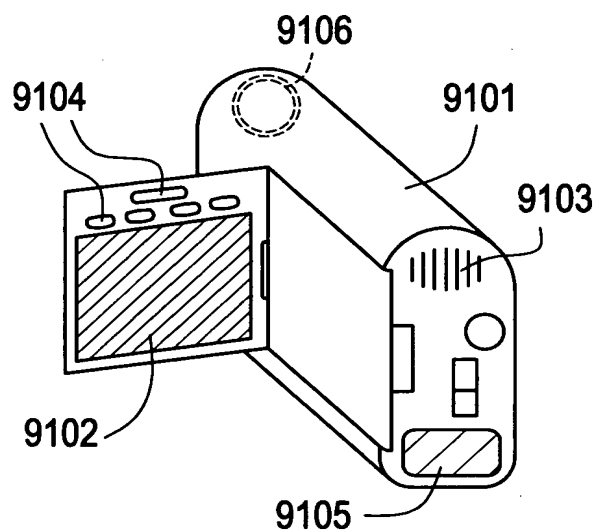


FIG. 31C

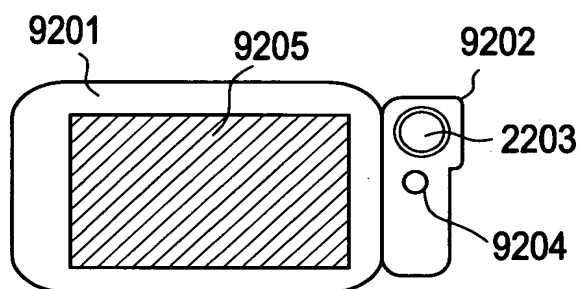


FIG. 31D

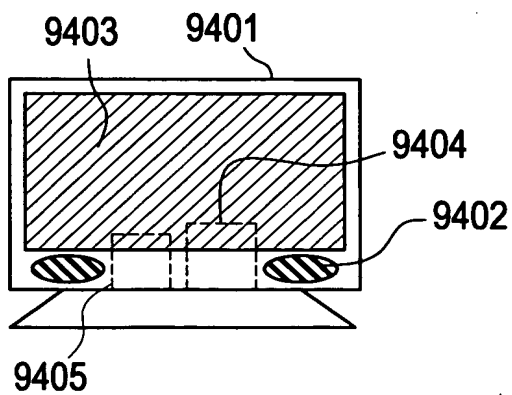
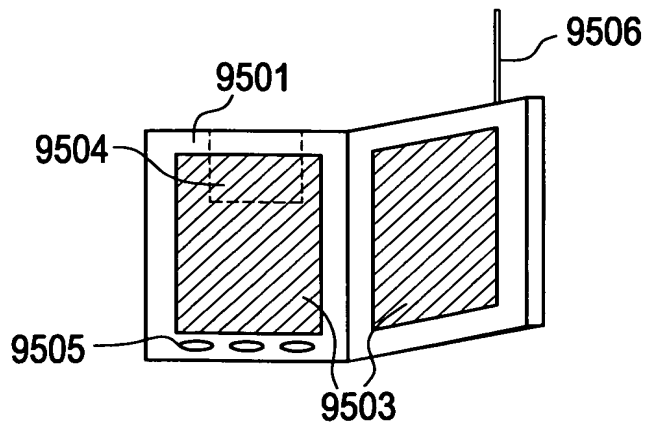


FIG. 31E





26/31

FIG. 32A

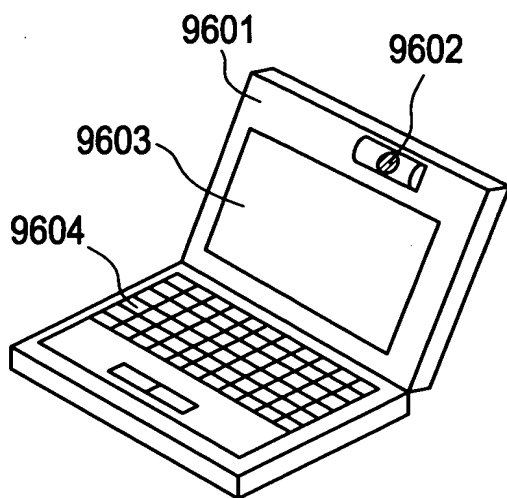


FIG. 32B

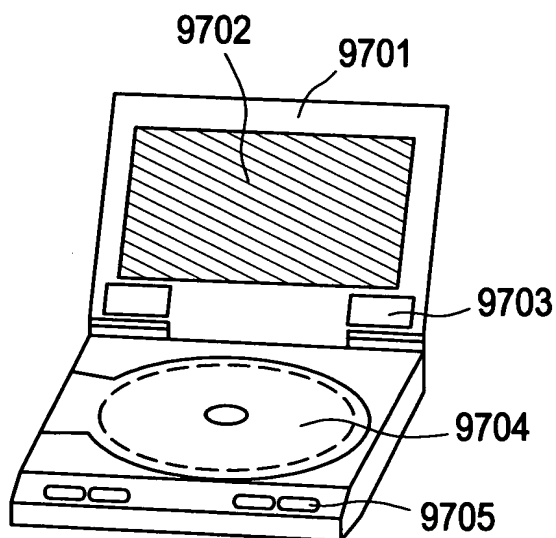
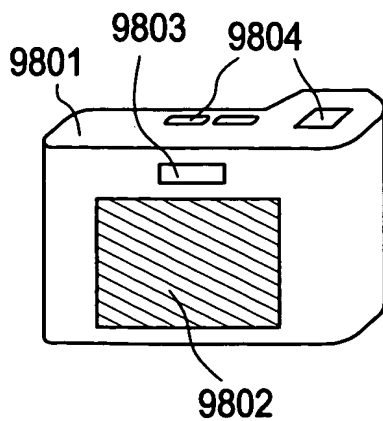


FIG. 32C





27/31

FIG. 33A

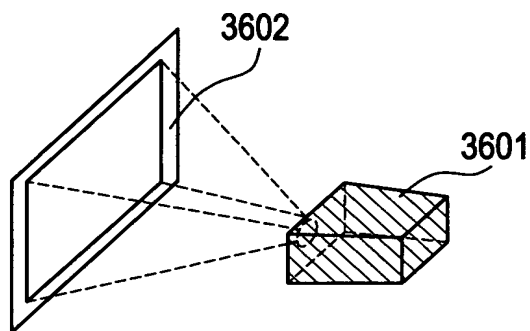


FIG. 33B

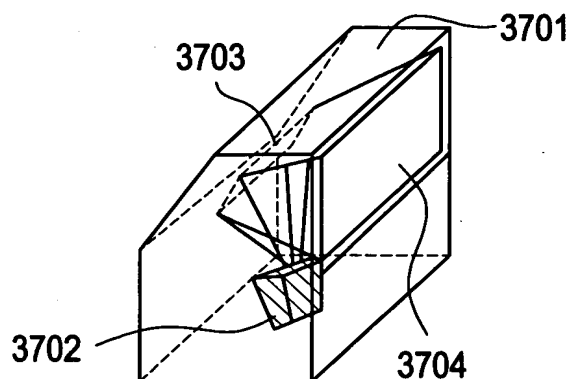


FIG. 33C

PROJECTING APPATUS (THREE PLATE TYPE)

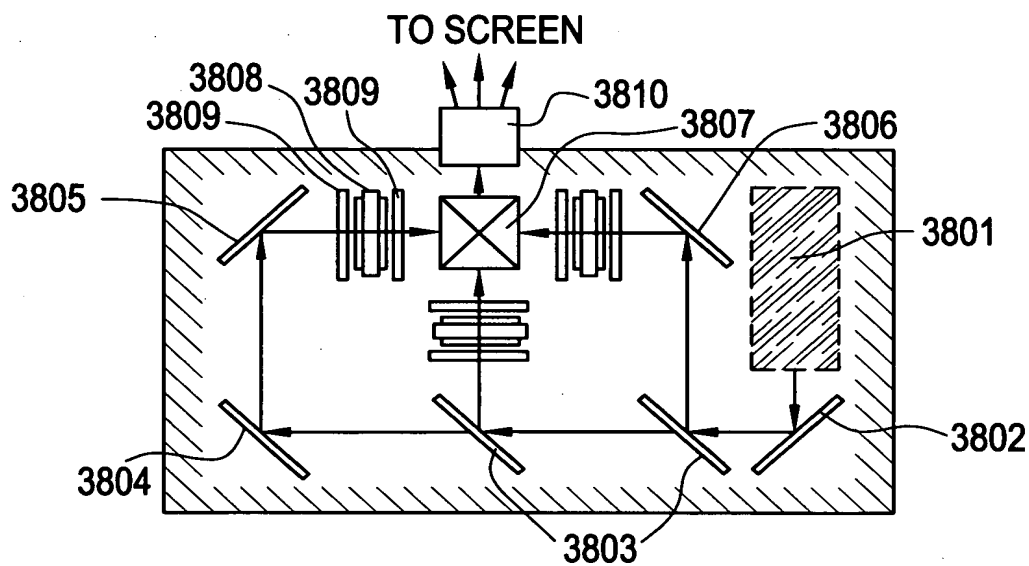
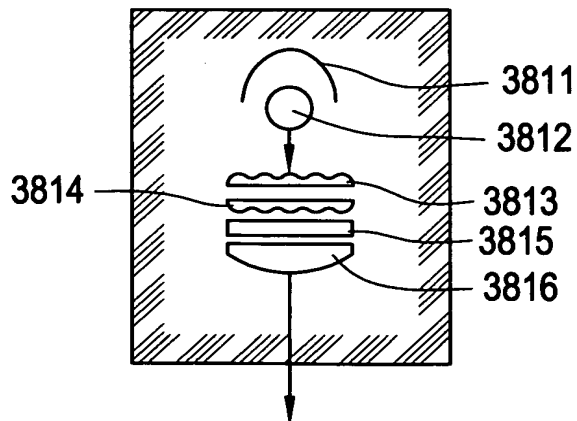


FIG. 33D

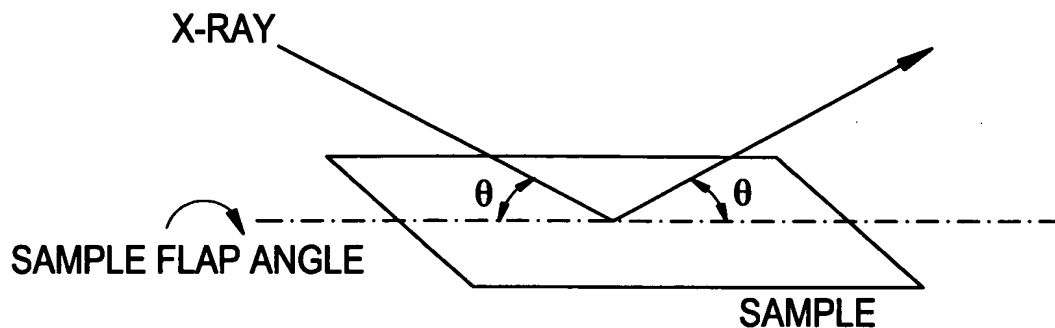
LIGHT SOURCE OPTICAL SYSTEM





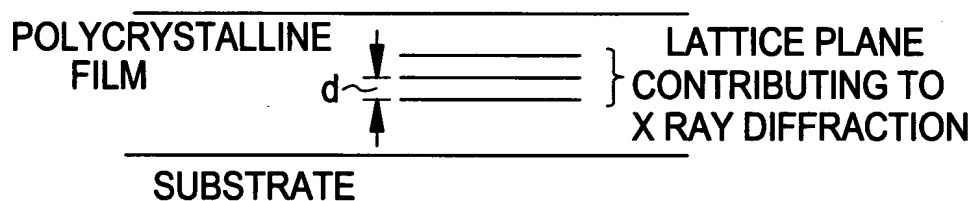
28/31

**FIG. 34**



**FIG. 35A**

IN CASE OF FLAP ANGLE  $0^\circ$



**FIG. 35B**

IN CASE OF FLAP ANGLE  $60^\circ$

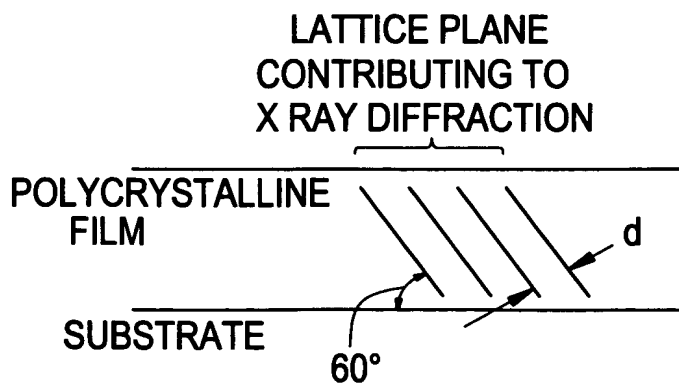
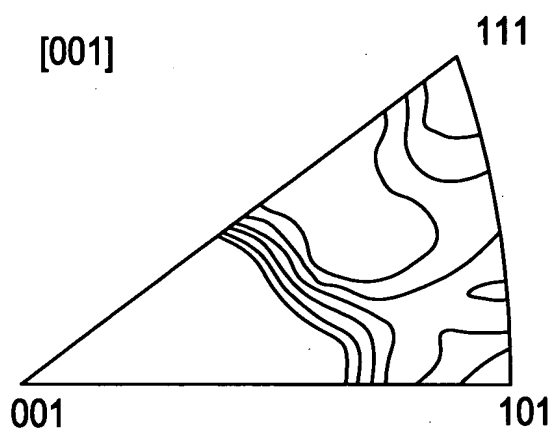


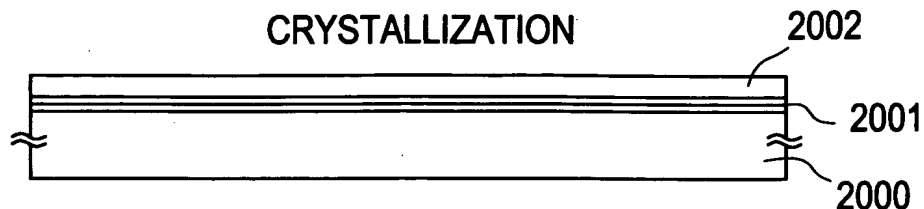


FIG. 36





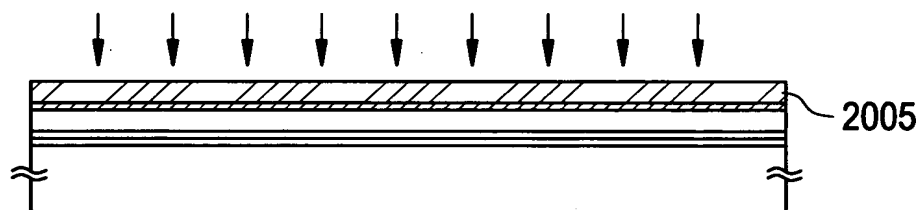
**FIG. 37A**  
CRYSTALLIZATION



**FIG. 37B**  
FORMATION OF BARRIER LAYER AND  
FORMATION OF SEMICONDUCTOR FILM



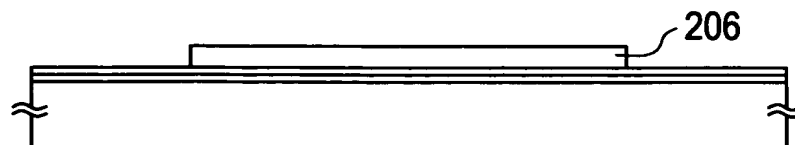
**FIG. 37C**  
DOPING WITH NOBLE GAS



**FIG. 37D**  
GETTERING



**FIG. 37E**  
FORMATION OF SEMICONDUCTOR ISLAND





31/31

FIG. 38

